KSN100P03X

-30V P-Channel MOSFET

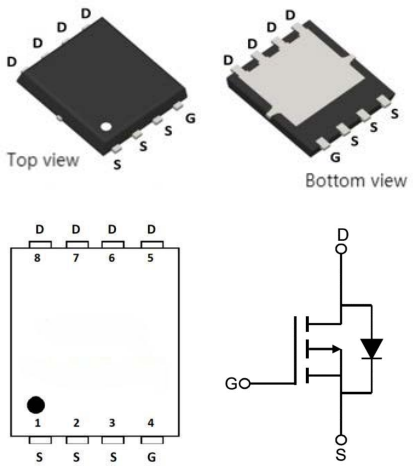
General Description

The KSN100P03X combines advanced trench MOSFET technology with a low resistance package to provide extremely low R_{DS}(ON). This device is ideal for load switch and battery protection applications.

Product Summary

V_{DS} (V)	$R_{DS(on)}$ (mΩ)	I_D (A)
-30	2.5at V_{GS} = 10 V	-125
	4.0atV_{GS} = 4.5 V	-90

PDFN5x6 Pin Configuration



Features

- Improved dv/dt capability
- Green Device Available
- Suit for 1.8V Gate Drive Applications

Applications

- Load Switch
- Battery protection
- Uninterruptible power supply

100% UIS TESTED!
100% ΔVds TESTED!

Absolute Maximum Ratings Tc=25℃ unless otherwise noted

Symbol	Parameter	Rating	Units
V_{DS}	Drain-Source Voltage	-30	V
V_{GS}	Gate-Source Voltage	±20	V
I_D	Drain Current – Continuous (T_C=25℃)	-125	A
	Drain Current – Continuous (T_C=100℃)	-70	A
I_{DM}	Drain Current – Pulsed[1]	-280	A
P_D	Power Dissipation (T_C=25℃)	85	W
	Power Dissipation – Derate above 25℃	0.63	W/℃
T_{STG}	Storage Temperature Range	-50 to 150	℃
T_J	Operating Junction Temperature Range	-50 to 150	℃

Thermal Characteristics

Symbol	Parameter	Typ.	Max.	Unit
$R_{\theta JA}$	Thermal Resistance Junction to ambient	---	61	℃/W
$R_{\theta JC}$	Thermal Resistance Junction to Case	---	1.17	℃/W

Electrical Characteristics (T_J=25 ℃, unless otherwise noted)

Off Characteristics

Symbol	Parameter	Conditions	Min.	Typ.	Max.	Unit
BV_{DSS}	Drain-Source Breakdown Voltage	V_{GS}=0V , I_D=250uA	-30	---	---	V
$\triangle BV_{DSS}/\triangle T_J$	BV_{DSS} Temperature Coefficient	Reference to 25℃ , I_D=1mA	---	0.01	---	V/℃
I_{DSS}	Drain-Source Leakage Current	V_{DS}=-20V , V_{GS}=0V , T_J=25℃	---	---	1	uA
		V_{DS}=-20V , V_{GS}=0V , T_J=125℃	---	---	10	uA
I_{GSS}	Gate-Source Leakage Current	V_{GS}=±20V , V_{DS}=0V	---	---	±100	nA

On Characteristics

$R_{DS(ON)}$	Static Drain-Source On-Resistance	V_{GS}=-10V , I_D=-20A	---	2.5	3.8	mΩ
		V_{GS}=-4.5V , I_D=-15A	---	4.0	6.0	mΩ
$V_{GS(th)}$	Gate Threshold Voltage	V_{GS}=V_{DS} , I_D =250uA	-1.2	-1.8	-2.6	V
$\triangle V_{GS(th)}$	$V_{GS(th)}$ Temperature Coefficient		---	4.3	---	mV/℃
gfs	Forward Transconductance	V_{DS}=-5V , I_S=-20A	---	30	---	S

Dynamic and switching Characteristics

Q_g	Total Gate Charge[2,3]	V_{DS}=-15V , V_{GS}=-10V , I_D=-20A	---	83	127	nC
Q_{gs}	Gate-Source Charge[2,3]		---	17	29	
Q_{gd}	Gate-Drain Charge[2,3]		---	21	36	
$T_{d(on)}$	Turn-On Delay Time[2,3]	V_{DS}=-15V , V_{GS}=-10V , R_G=3.3 Ω I_D=-10A	---	16	27	ns
T_r	Rise Time[2,3]		---	21	33	
$T_{d(off)}$	Turn-Off Delay Time[2,3]		---	73	105	
T_f	Fall Time[2,3]		---	62	86	
C_{iss}	Input Capacitance	V_{DS}=-15V , V_{GS}=0V , F=1MHz	---	4861	5630	pF
C_{oss}	Output Capacitance		---	347	634	
C_{rss}	Reverse Transfer Capacitance		---	183	260	

Drain-Source Diode Characteristics and Maximum Ratings

Symbol	Parameter	Conditions	Min.	Typ.	Max.	Unit
I_S	Continuous Source Current	V_G=V_D=0V , Force Current	---	---	-70	A
I_{SM}	Pulsed Source Current		---	---	-160	A
V_{SD}	Diode Forward Voltage	V_{GS}=0V , I_S=-1A , T_J=25℃	---	---	-1.2	V

Note :
1. Repetitive Rating : Pulsed width limited by maximum junction temperature.
2. The data tested by pulsed , pulse width ≦ 300us , duty cycle ≦ 2%.
3. Essentially independent of operating temperature.

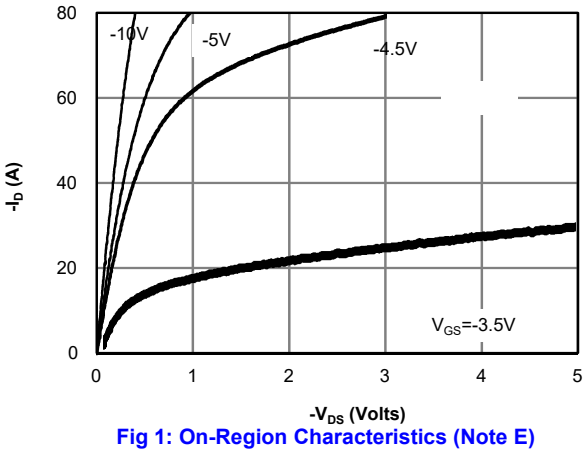


Fig 1: On-Region Characteristics (Note E)

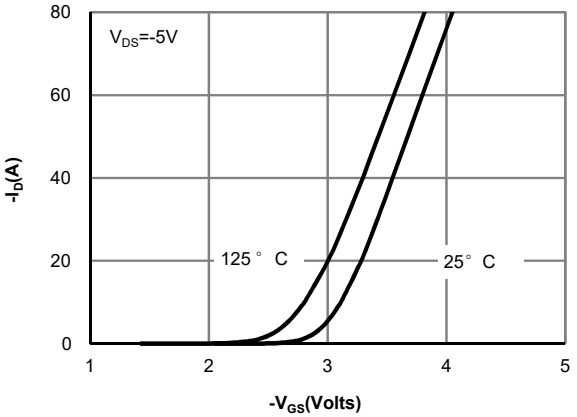


Figure 2: Transfer Characteristics (Note E)

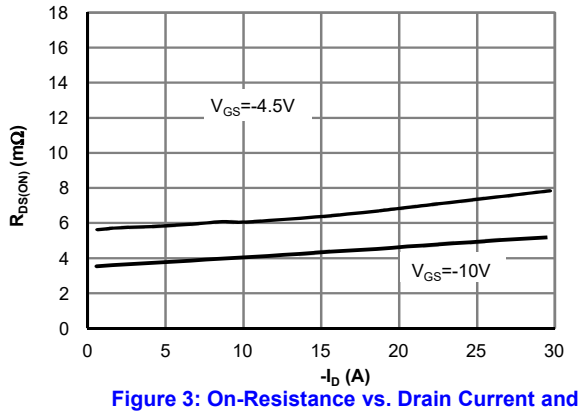


Figure 3: On-Resistance vs. Drain Current and Gate Voltage (Note E)

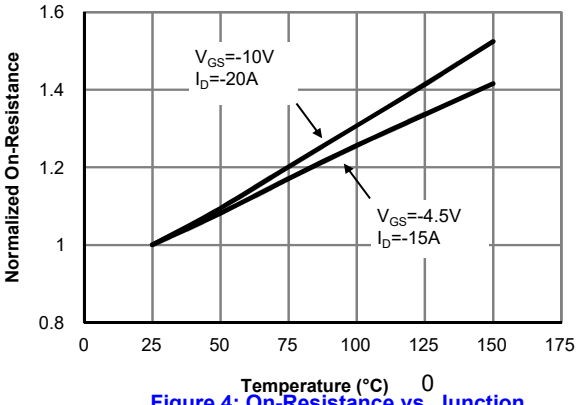


Figure 4: On-Resistance vs. Junction Temperature (Note E)

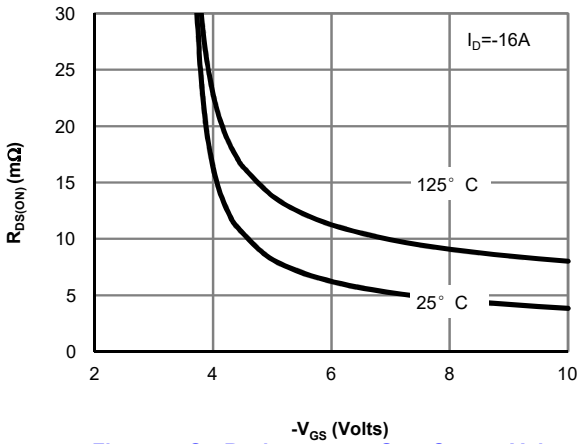


Figure 5: On-Resistance vs. Gate-Source Voltage (Note E)

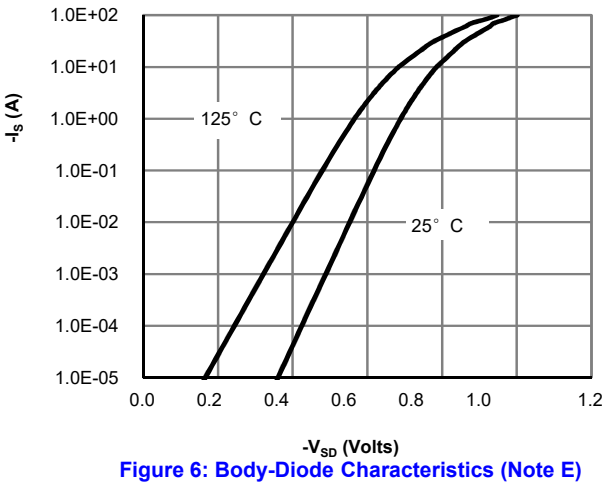


Figure 6: Body-Diode Characteristics (Note E)

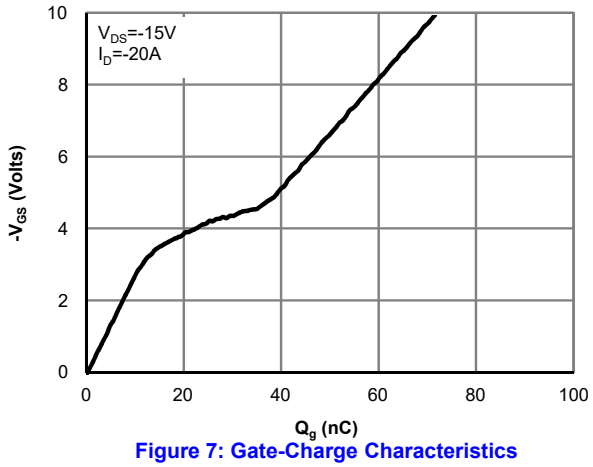


Figure 7: Gate-Charge Characteristics

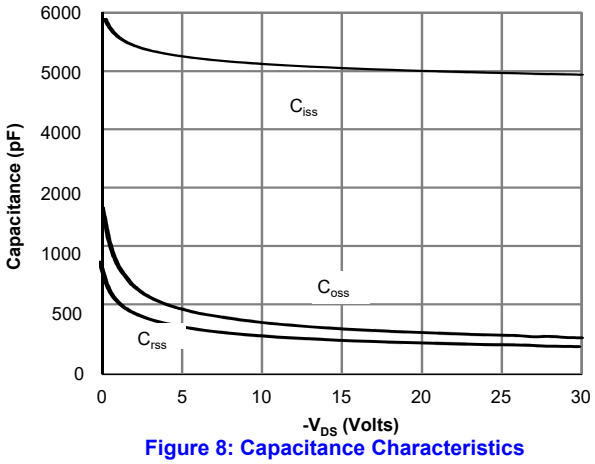


Figure 8: Capacitance Characteristics

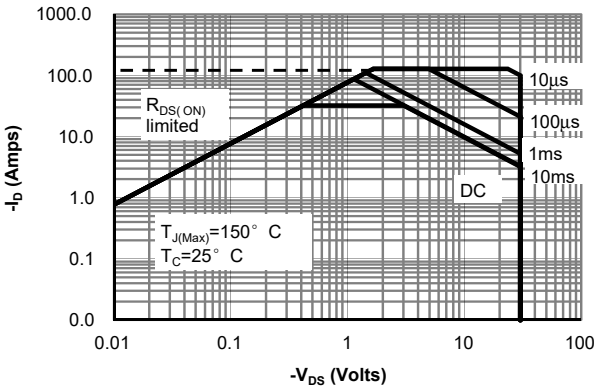


Figure 9: Maximum Forward Biased Safe **Operating Area (Note F)**

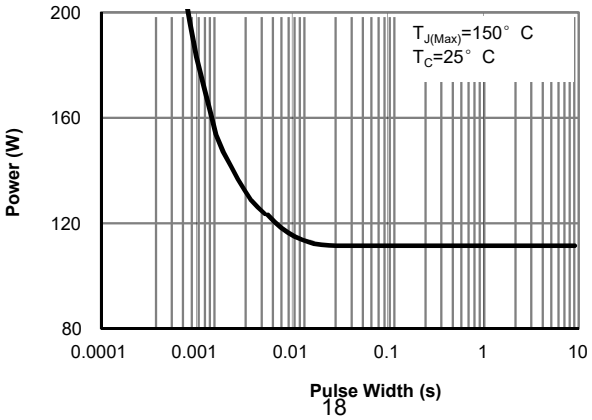


Figure 10: Single Pulse Power Rating Junction-to-Cas **(Note F)**

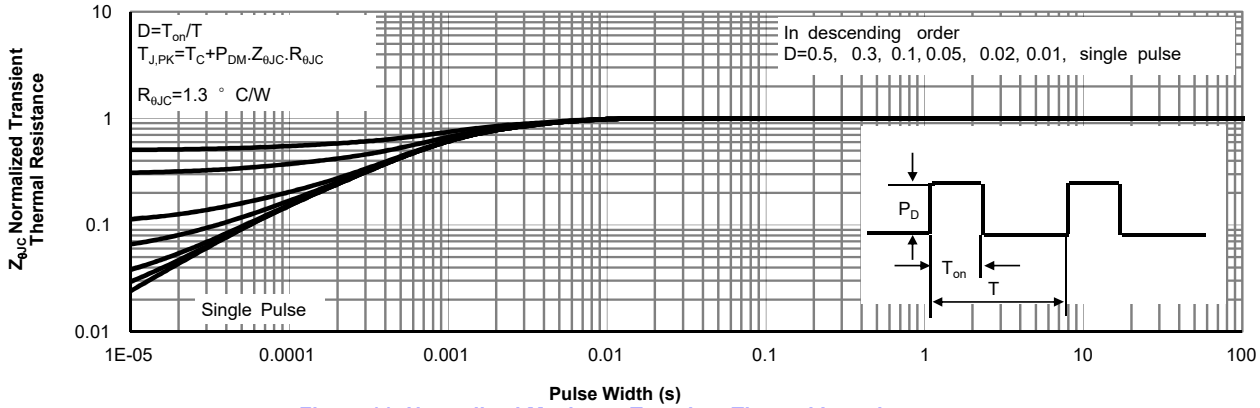


Figure 11: Normalized Maximum Transient Thermal Impedance **(Note F)**

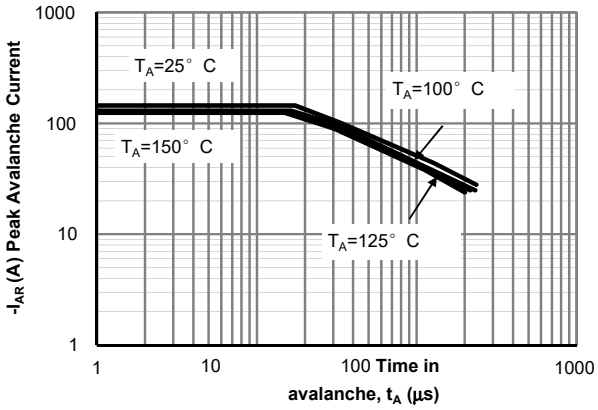


Figure 12: Single Pulse Avalanche capability (Note C)

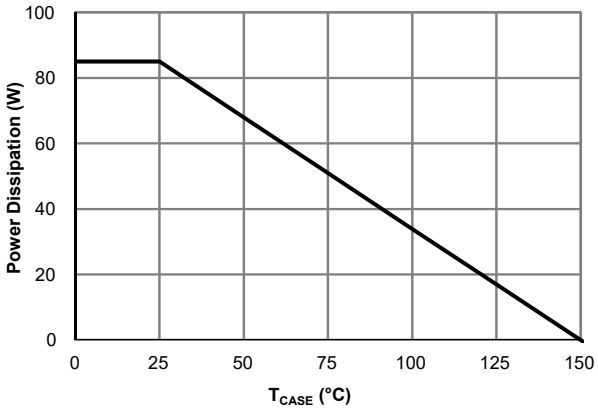


Figure 13: Power De-rating (Note F)

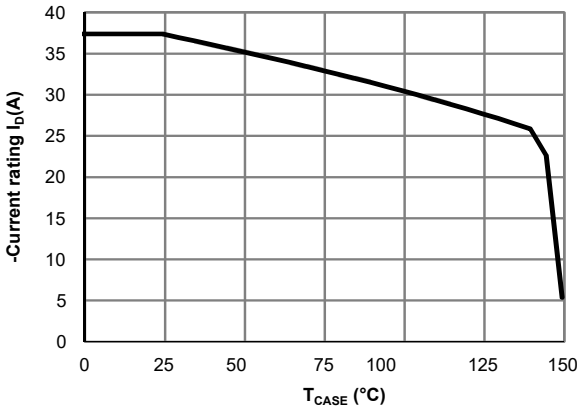


Figure 14: Current De-rating (Note F)

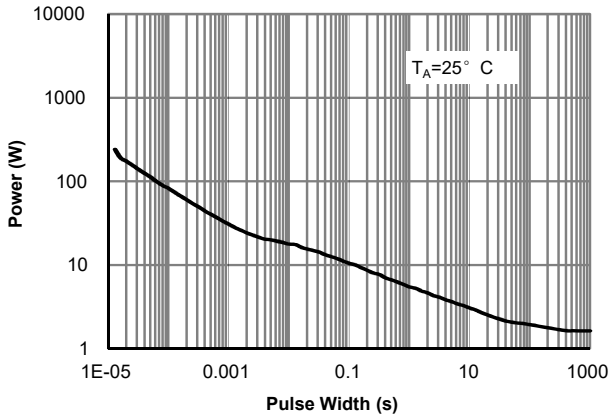


Figure 15: Single Pulse Power Rating Junction-to-Ambient (Note H)

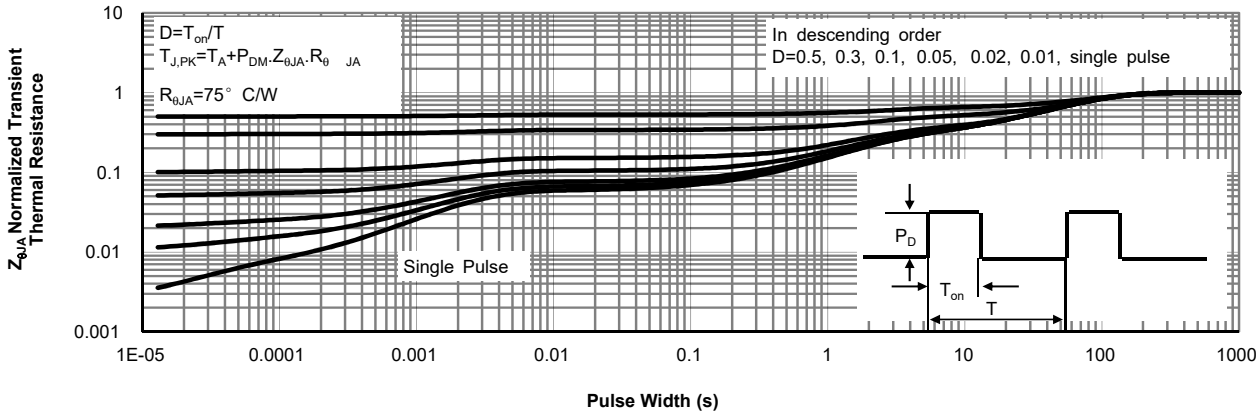


Figure 16: Normalized Maximum Transient Thermal Impedance (Note H)

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